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ПОГЛАВЉА У МЕЂУНАРОДНИМ МОНОГРАФИЈАМА

1. Z. Stamenković and **N. Stojadinović**, "Computer-Aided Analysis and Forecast of Integrated Circuit Yield", in "*The Computer Engineering Handbook*", edited by V. Oklobžija, CRC Press, Boca Raton, pp. 47.1-47.24 (2001) ISBN-10: 0849308852 ISBN-13: 978-0849308857
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3. D. Danković, I. Manić, S. Djorić-Veljković, V. Davidović, S. Golubović, and **N. Stojadinović**, "Implications of Negative Bias Temperature Instability in Power MOS Transistors" in *Micro Electronic and Mechanical Systems*, edited by Kenichi Takahata, IN-TECH Press, Boca Raton, pp. 19.319-19.342 (2009) ISBN: 978-953-307-027-8
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